

Thyristor Modules

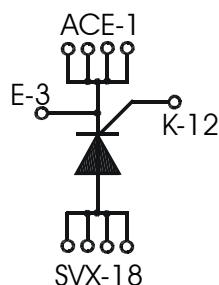
ECO-PAC 2

$$I_{TRMS} = 200 \text{ A}$$

$$I_{TAVM} = 130 \text{ A}$$

$$V_{RRM} = 1200/1600 \text{ V}$$

V_{RSM}	V_{RRM}	
V_{DSM}	V_{DRM}	Typ
V	V	
1300	1200	VCO 132-12io7
1700	1600	VCO 132-16io7



Symbol	Conditions	Maximum Ratings
I_{TRMS}		200 A
I_{TAVM}	$T_C = 85^\circ\text{C}; T_{VJ} = 130^\circ\text{C}; 180^\circ \text{ sine}$	130 A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	3600 A
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	3850 A
	$T_{VJ} = 125^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	3200 A
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	3420 A
I^2t	$T_{VJ} = 45^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	64 800 A ² s
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	62 300 A ² s
	$T_{VJ} = 125^\circ\text{C}; t = 10 \text{ ms (50 Hz)}$	51 200 A ² s
	$V_R = 0; t = 8.3 \text{ ms (60 Hz)}$	49 100 A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C};$ repetitive, $I_T = 250 \text{ A}$ $f = 50 \text{ Hz}; t_p = 200 \mu\text{s};$	150 A/ μs
	$V_D = \frac{2}{3} V_{DRM};$ $I_G = 0.5 \text{ A};$ non repetitive, $I_T = I_{TAVM}$ $di_G/dt = 0.5 \text{ A}/\mu\text{s}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}; V_D = \frac{2}{3} V_{DRM};$ $R_{GK} = \infty;$ method 1 (linear voltage rise)	1000 V/ μs
P_{GM}	$T_{VJ} = 125^\circ\text{C}; t_p = 30 \text{ ms}$	$\leq 10 \text{ W}$
	$I_T = I_{T(AV)M}; t_p = 300 \text{ ms}$	$\leq 5 \text{ W}$
P_{GAVM}		0.5 W
V_{RGM}		10 V
T_{VJ}		-40...+130 °C
T_{VJM}		150 °C
T_{stg}		-40...+125 °C
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	3000 V~
	$I_{ISOL} \leq 1 \text{ mA} t = 1 \text{ s}$	3600 V~
M_d	Mounting torque (M4)	1.5 - 2.0 Nm 14 - 18 lb.in.
Weight	Typical including screws	24 g

Features

- Isolation voltage 3600 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

- DC Motor control
- Light and temperature control
- Softstart AC motor controller
- Solid state switches

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling
- High power density
- Small and light weight

Data according to IEC 60747 and refer to a single diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

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Symbol	Conditions	Characteristic Values	
		typ.	max.
I_D, I_R	$V_R / V_D = V_{RRM} / V_{DRM}$ $T_{VJ} = 125^\circ\text{C}$	10	mA
V_T	$I_T = 200\text{ A}$ $T_{VJ} = 25^\circ\text{C}$	1.3	V
V_{T0}	For power-loss calculations only	0.80	V
r_t		1.65	mΩ
V_{GT}	$V_D = 6\text{ V}$ $T_{VJ} = 25^\circ\text{C}$	1.5	V
I_{GT}	$V_D = 6\text{ V}$ $T_{VJ} = -40^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	1.6 300 400	V mA mA
V_{GD}	$V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = 125^\circ\text{C}$	0.2	V
I_{GD}		10	mA
I_L	$t_p = 10\text{ }\mu\text{s}$; $I_G = 0.5\text{ A}$; $di_G/dt = 0.5\text{ A}/\mu\text{s}$ $T_{VJ} = 25^\circ\text{C}$	450	mA
I_H	$V_D = 6\text{ V}$; $R_{GK} = \infty$; $T_{VJ} = 25^\circ\text{C}$	200	mA
t_{gd}	$V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.5\text{ A}$; $di_G/dt = 0.5\text{ A}/\mu\text{s}$ $T_{VJ} = 25^\circ\text{C}$	2	μs
R_{thJC}	per thyristor; DC current	0.25	K/W
R_{thJH}		0.35	K/W
d_s	Creeping distance on surface	11.2	mm
d_A	Creepage distance in air	5.0	mm
a	Maximum allowable acceleration	50	m/s ²

Dimensions in mm (1 mm = 0.0394")

